The Conference Theme

"Nanotechnology and Its Impact on Electron Devices"

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([1]University of Hyogo, [2]Meiji University, [3]National Institute for Materials Science)

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Y. Uenishi[1], K. Kozono[1], S. Mitani[2], Y. Nakano[2], T. Nakamura[2], T.

Hosoi[1], T. Shimura[1], H. Watanabe[1] (Osaka University, [1] ROHM CO., LTD[2].)

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([1]Osaka Institute of Technology, [2]The Wakasa Wan Energy Research Center)

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([1]Osaka Institute of Technology, [2]The Wakasa Wan Energy

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Keynote Speeches (II)

10:00-10:40

K-4 **(p.22)** The Role of High-Doped Source and Drain on Device Performance in Nano-Scale Si-MOSFETs
N. Sano (University of Tsukuba)

Short Break (10:40-10:50)

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H. Inokawa (Shizuoka University)

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Technical Session A (Silicon Devices and Related)

13:30-13:50

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T. Doe[1,2], M. Horita[1,2], T. Nishida[1,2], Y. Ishikawa[1,2], Y. Uraoka[1,2]
([1]NIST, [2]CREST)

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A-2 **(p.34)** Electrical and Structural Properties of Organic Thin-Film Transistor using Very Thin Pentacene Film
A. Heya[1], N. Matsuo[1], T. Konaganezawa[2]
([1]University of Hyogo, [2]Japan Synchrotron Radiation Research Institute)

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A-3 **(p.36)** Tight Binding Modeling of Intermediate Band Solar Cells Based on InAs/GaAs Quantum Dot Arrays
A. Mehdipour, M. Ogawa, S. Souma (Kobe University)

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Technical Session B
(Silicon Devices and Related)

14:45-15:05

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Y. Yamamoto, T. Yamaguchi, Y. Kawasaki, S. Kudo, J. Tsuchimoto, K. Sato, Y. Nishida, T. Yamashita, H. Oda, Y. Inoue (Renesas Electronics Corp.)

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([1]Low-power Electronics Association & Project, [2]Renesas Electronics Corp.)

Break (15:25-15:40)

15:40-16:00

B-3 **(p.44)** An Estimation of Inversion-Layer EOT Influenced by Quantum Effects for Sub-20nm MOSFETs
M. Yamamoto, A. Hiroki, J-C. Yoon (Kyoto Institute of Technology)

16:00-16:20

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K. Yamasaki[1], E. Machida[1], M. Horita[1,2], Y. Ishikawa[1,2], Y. Uraoka[1,2]
([1]NIST, [2]CREST)

Break (16:20-16:40)

Special Invited Session

16:40-17:20

T-1 **(p.28)** On-chip Robotics for Biomedical Innovations
F. Arai (Nagoya University)

Short Break (17:20-17:30)

Awards & Closing Remark

17:30-17:40 Award Presentation: Y. Ohmura (Kansai University)
17:40-17:50 Closing Remark: Y. Ohmura (Kansai University)